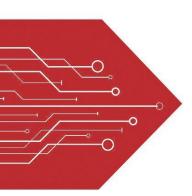
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data speet



Semiconductor

Compiance

Features

- Solid-state silicon-avalanche technology
- Low operating and clamping voltage
- Up to four I/O Lines of Protection
- Ultra low capacitance: 0.3pF typical(I/O to I/O)
- Low Leakage
- Low operating voltage:5V
- Flow-Through design

IEC COMPATIBILITY (EN61000-4)

- IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20μs)

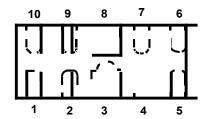
Mechanical Characteristics

- DFN2510-10L
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Applications

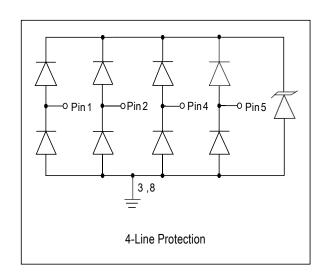
- Digital Visual Interface(DVI)
- MDDI Ports
- DisplayPortTM Interface
- PCI Express
- High Definition Multi-Media Interface(HDMI)
- eSATA Interfaces

DFN2510-10L



Pin	Identificaion
1,2,4,5	Input Lines
6,7,9,10	Output Lines (No Internal Connection)
3,8	Ground

Circuit Diagram









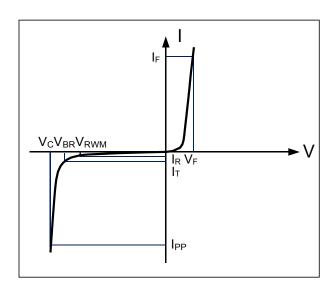


Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20μs)	P _{PP}	150	Watts
Peak Pulse Current (t _p =8/20μs)	I _{pp}	5	А
ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2(contact)	V _{ESD}	+/-17 +/-12	kV
Operating Temperature	TJ	-55 to + 125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Electrical Parameters (T=25°C)

Symbol	Parameter
I PP	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
VRWM	Working Peak Reverse Voltage
IR	Maximum Reverse Leakage Current @ Vким
V _{BR}	Breakdown Voltage @ I⊤
lτ	Test Current
lF	Forward Current
VF	Forward Voltage @ I _F

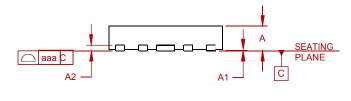


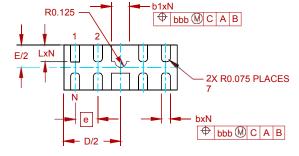
Electrical Characteristics

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V _{RWM}	Any I/O pin to ground			5.0	V
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA Any I/O pin to ground	6.0			V
Reverse Leakage Current	I _R	V _{RWM} = 5V, T=25°C Any I/O pin to ground			1	μA
Clamping Voltage	Vc	I _{pp} =5A, t _p =8/20µs Any I/O pin to ground			15	V
		V _R = 0V, f = 1MHz I/O pin to GND			0.8	pF
Junction Capacitance	C _j	V _R = 0V, f = 1MHz Between I/O pins		0.3		pF

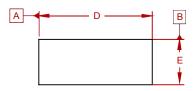


PACKAGE MECHANICAL DATA



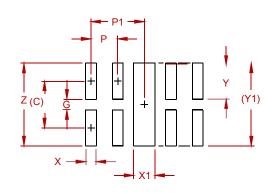


Dimensions in millimeters



DIMENSI ONS						
DIM INCHES		MILLIMETERS				
J	MIN	NOM	MAX	MIN	NOM	MAX
Α	.020	.023	.026	0.50	0.58	0.65
A1	0.00	.001	.002	0.00	0.03	0.05
A2	(.005)		(0	.13)		
b	.006	.008	.010	0.15	0.20	0.25
b1	.014	.016	.018	0.35	0.40	0.45
D	.094	.098	.102	2.40	2.50	2.60
Е	.035	.039	.043	0.90	1.00	1.10
е	.020 BSC		0.50	BSC		
L	.012	.015	.017	0.30	0.38	0.425
N	8		8			
aaa	.003		0.08			
bbb	.004		0.10			

Suggested Pad Layout



DIMENSIONS			
DIM	INCHES	MILLIMETERS	
С	(.034)	(0.875)	
G	.008	0.20	
Р	.020	0.50	
P1	.039	1.00	
Х	.008	0.20	
X1	.016	0.40	
Y	.027	0.675	
Y1	(.061)	(1.55)	
Z	.061	1.55	

NOTES:

CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES). THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
ESDA6V8UD-MS	DFN2510-10L	3000



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